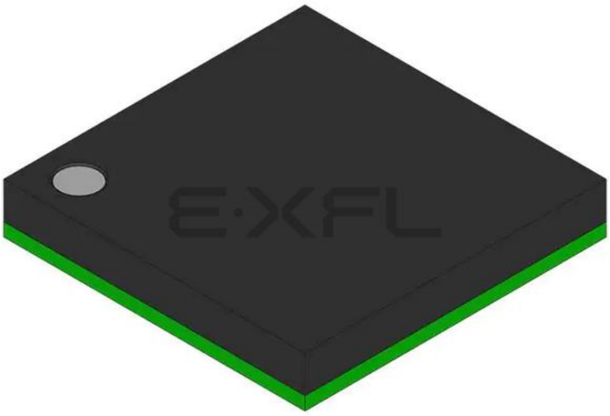

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	64
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 24x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	121-LFBGA
Supplier Device Package	121-MAPBGA (8x8)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mk11dn512vmc5

1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to freescale.com and perform a part number search for the following device numbers: PK11 and MK11 .

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Format

Part numbers for this device have the following format:

Q K## A M FFF R T PP CC N

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	• M = Fully qualified, general market flow • P = Prequalification
K##	Kinetis family	• K11
A	Key attribute	• D = Cortex-M4 w/ DSP • F = Cortex-M4 w/ DSP and FPU
M	Flash memory type	• N = Program flash only • X = Program flash and FlexMemory

Table continues on the next page...

Field	Description	Values
Q	Qualification status	• M = Fully qualified, general market flow • P = Prequalification
C	Speed	• G = 50 MHz
F	Flash memory configuration	• G = 128 KB + Flex • H = 256 KB + Flex • 9 = 512 KB
T	Temperature range (°C)	• V = –40 to 105
PP	Package identifier	• MC = 121 MAPBGA

This tables lists some examples of small package marking along with the original part numbers:

Original part number	Alternate part number
MK11DX128VLK5	M11GGVLK
MK11DX256VMC5	M11GHVMC

3 Terminology and guidelines

3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

3.1.1 Example

This is an example of an operating requirement:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	0.9	1.1	V

4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	-2000	+2000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105°C	-100	+100	mA	3

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.
3. Determined according to JEDEC Standard JESD78, *IC Latch-Up Test*.

4.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V
I_{DD}	Digital supply current	—	155	mA
V_{DIO}	Digital input voltage (except $\overline{\text{RESET}}$, EXTAL, and XTAL)	–0.3		V
V_{AIO}	Analog[1], $\overline{\text{RESET}}$, EXTAL, and XTAL input voltage	–0.3	V_{DD} + 0.3	V
I_D	Maximum current single pin limit (applies to all digital pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V
VREGIN	USB regulator input	–0.3	6.0	V
V_{BAT}	RTC battery supply voltage	–0.3	3.8	V

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

5 General

Table 1. Voltage and current operating requirements (continued)

Symbol	Description	Min.	Max.	Unit	Notes
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins • Negative current injection • Positive current injection	-25 —	— +25	mA	
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

1. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is less than V_{AIO_MIN} or greater than V_{AIO_MAX}, a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO\_MIN}-V_{IN})/|I_{ICAIO}|$. The positive injection current limiting resistor is calculated as $R=(V_{IN}-V_{AIO\_MAX})/|I_{ICAIO}|$. Select the larger of these two calculated resistances if the pin is exposed to positive and negative injection currents.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
	Low-voltage warning thresholds — high range					1
V_{LVW1H}	• Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V_{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V_{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	80	—	mV	
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V_{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V_{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V_{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	60	—	mV	
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

1. Rising threshold is the sum of falling threshold and hysteresis voltage

Table 3. VBAT power operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR_VBAT}	Falling VBAT supply POR detect voltage	0.8	1.1	1.5	V	

5.2.3 Voltage and current operating behaviors

Table 4. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{OH}	Output high voltage — high drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, I_{OH} = - 9 mA	$V_{DD} - 0.5$	—	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, I_{OH} = -3 mA	$V_{DD} - 0.5$	—	V	
	Output high voltage — low drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, I_{OH} = -2 mA	$V_{DD} - 0.5$	—	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, I_{OH} = -0.6 mA	$V_{DD} - 0.5$	—	V	
I_{OHT}	Output high current total for all ports	—	100	mA	
V_{OL}	Output low voltage — high drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, I_{OL} = 9 mA	—	0.5	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, I_{OL} = 3 mA	—	0.5	V	
	Output low voltage — low drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, I_{OL} = 2 mA	—	0.5	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, I_{OL} = 0.6 mA	—	0.5	V	
I_{OLT}	Output low current total for all ports	—	100	mA	
I_{IN}	Input leakage current (per pin)				1
	• @ full temperature range	—	1.0	μA	
	• @ 25 °C	—	0.1	μA	
I_{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	μA	
I_{OZ}	Total Hi-Z (off-state) leakage current (all input pins)	—	4	μA	
R_{PU}	Internal pullup resistors	22	50	kΩ	2
R_{PD}	Internal pulldown resistors	22	50	kΩ	3

1. Tested by ganged leakage method
2. Measured at Vinput = V_{SS}
3. Measured at Vinput = V_{DD}

5.2.4 Power mode transition operating behaviors

All specifications except t_{POR}, and VLLSx→RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 50 MHz
- Bus clock = 50 MHz
- Flash clock = 25 MHz
- MCG mode: FEI

Table 5. Power mode transition operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip. • 1.71 V/(V_{DD} slew rate) ≤ 300 μs • 1.71 V/(V_{DD} slew rate) > 300 μs	 — —	 300 1.7 V / (V_{DD} slew rate)	μs	1
	• VLLS0 → RUN	—	135	μs	
	• VLLS1 → RUN	—	135	μs	
	• VLLS2 → RUN	—	85	μs	
	• VLLS3 → RUN	—	85	μs	
	• LLS → RUN	—	6	μs	
	• VLPS → RUN	—	5.2	μs	
	• STOP → RUN	—	5.2	μs	

1. Normal boot (FTFL_OPT[LPBOOT]=1)

5.2.5 Power consumption operating behaviors

Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash • @ 1.8 V • @ 3.0 V	 — —	 12.98 12.93	 14 13.8	 mA mA	2

Table continues on the next page...

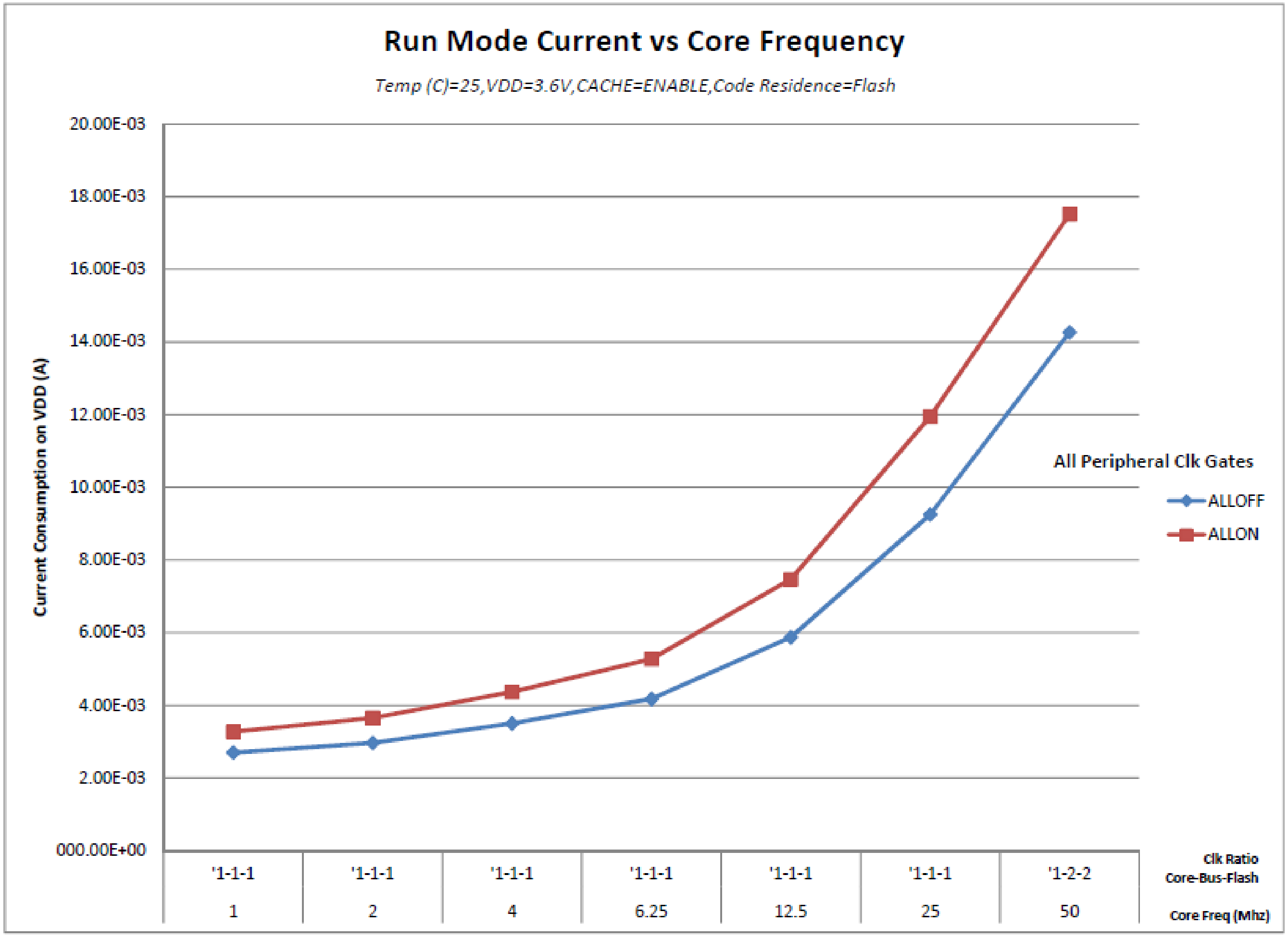

Figure 2. Run mode supply current vs. core frequency

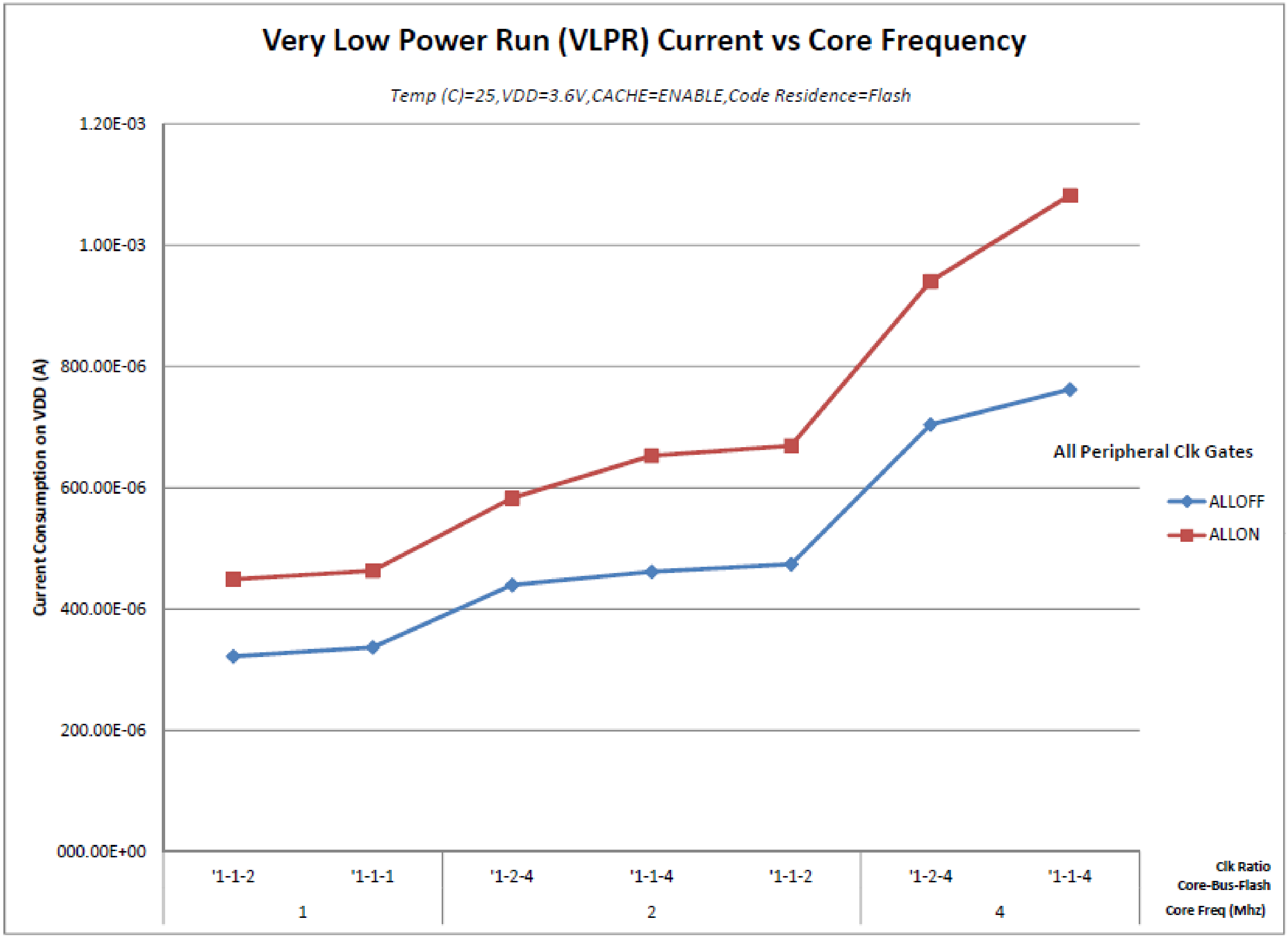

Figure 3. VLPR mode supply current vs. core frequency

5.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors [1]

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	19	dBμV	2, 3
V_{RE2}	Radiated emissions voltage, band 2	50–150	21	dBμV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	19	dBμV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	11	dBμV	
V_{RE_IEC}	IEC level	0.15–1000	L	—	3, 4

1. This data was collected on a MK20DN128VLH5 64pin LQFP device.
2. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

3. V_{DD} = 3.3 V, T_A = 25 °C, f_{OSC} = 12 MHz (crystal), f_{SYS} = 48 MHz, f_{BUS} = 48MHz
4. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

5.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.freescale.com.
2. Perform a keyword search for “EMC design.”

5.2.8 Capacitance attributes

Table 8. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF

5.3 Switching specifications

5.3.1 Device clock specifications

Table 9. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
Normal run mode					
f_{SYS}	System and core clock	—	50	MHz	
f_{BUS}	Bus clock	—	50	MHz	
f_{FLASH}	Flash clock	—	25	MHz	
f_{LPTMR}	LPTMR clock	—	25	MHz	
VLPR mode[1]					
f_{SYS}	System and core clock	—	4	MHz	
f_{BUS}	Bus clock	—	4	MHz	
f_{FLASH}	Flash clock	—	1	MHz	
f_{ERCLK}	External reference clock	—	16	MHz	
f_{LPTMR_pin}	LPTMR clock	—	25	MHz	
f_{LPTMR_ERCLK}	LPTMR external reference clock	—	16	MHz	
f_{I2S_MCLK}	I2S master clock	—	12.5	MHz	
f_{I2S_BCLK}	I2S bit clock	—	4	MHz	

5.4 Thermal specifications

5.4.1 Thermal operating requirements

Table 11. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	–40	125	°C
T_A	Ambient temperature	–40	105	°C

5.4.2 Thermal attributes

Board type	Symbol	Description	121 MAPBGA	Unit	Notes
Single-layer (1s)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	79	°C/W	1, 2
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	46	°C/W	1, 3
Single-layer (1s)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	67	°C/W	1,3
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	42	°C/W	1,3
—	$R_{\theta JB}$	Thermal resistance, junction to board	29	°C/W	4
—	$R_{\theta JC}$	Thermal resistance, junction to case	21	°C/W	5
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	4	°C/W	6

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)* with the single layer board horizontal. For the LQFP, the board meets the JESD51-3 specification. For the MAPBGA, the board meets the JESD51-9 specification.

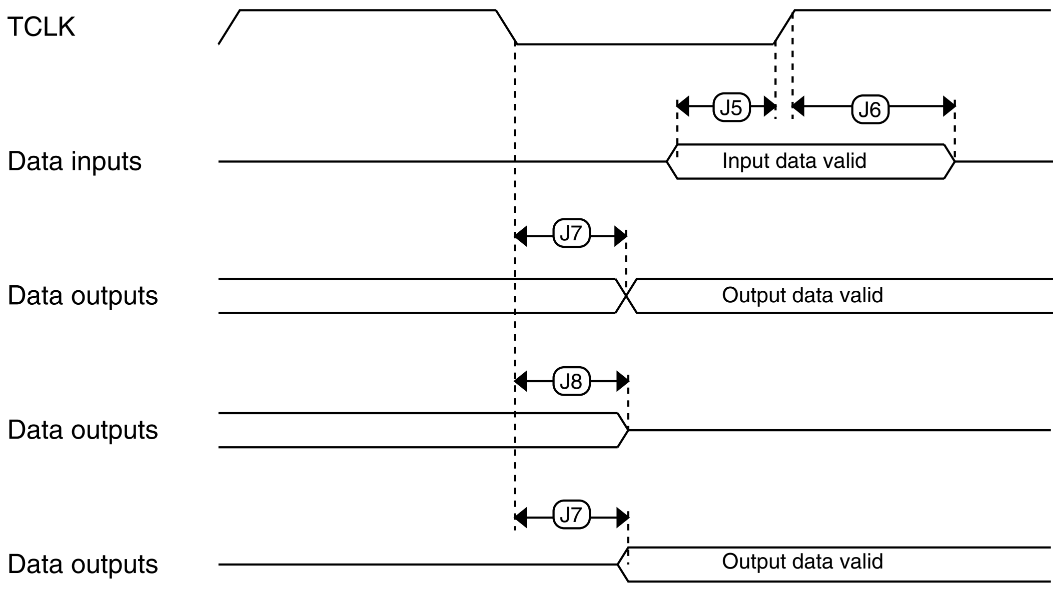

Figure 5. Boundary scan (JTAG) timing

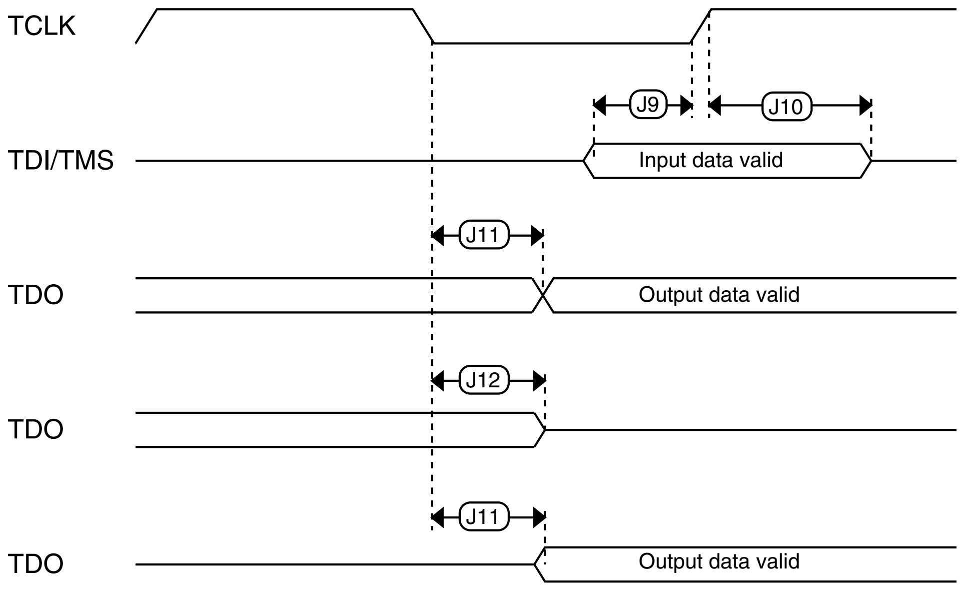

Figure 6. Test Access Port timing

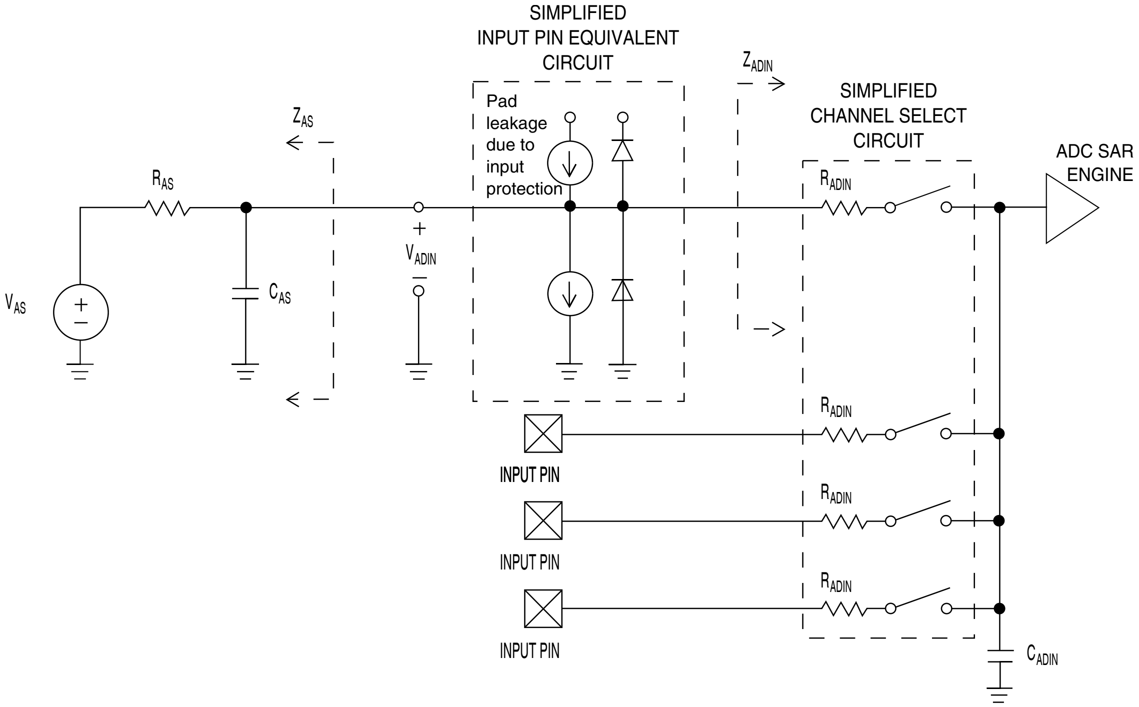

Figure 9. ADC input impedance equivalency diagram

6.6.1.2 16-bit ADC electrical characteristics

Table 25. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions[1].	Min.	Typ.[2]	Max.	Unit	Notes
I_{DDA_ADC}	Supply current		0.215	—	1.7	mA	3
f_{ADACK}	ADC asynchronous clock source	• ADLPC = 1, ADHSC = 0 • ADLPC = 1, ADHSC = 1 • ADLPC = 0, ADHSC = 0 • ADLPC = 0, ADHSC = 1	1.2 2.4 3.0 4.4	2.4 4.0 5.2 6.2	3.9 6.1 7.3 9.5	MHz MHz MHz MHz	$t_{ADACK} = 1/f_{ADACK}$
	Sample Time	See Reference Manual chapter for sample times					
TUE	Total unadjusted error	• 12-bit modes • <12-bit modes	— —	±4 ±1.4	±6.8 ±2.1	LSB[4]	5
DNL	Differential non-linearity	• 12-bit modes • <12-bit modes	— —	±0.7 ±0.2	-1.1 to +1.9 -0.3 to 0.5	LSB[4]	5
INL	Integral non-linearity	• 12-bit modes • <12-bit modes	— —	±1.0 ±0.5	-2.7 to +1.9 -0.7 to +0.5	LSB[4]	5
E_{FS}	Full-scale error	• 12-bit modes • <12-bit modes	— —	-4 -1.4	-5.4 -1.8	LSB[4]	$V_{ADIN} = V_{DDA}$ 5

Table continues on the next page...

6.6.2 CMP and 6-bit DAC electrical specifications

Table 26. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	μA
I_{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	μA
V_{AIN}	Analog input voltage	V_{SS} – 0.3	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis[1] • CR0[HYSTCTR] = 00 • CR0[HYSTCTR] = 01 • CR0[HYSTCTR] = 10 • CR0[HYSTCTR] = 11	 — — — —	 5 10 20 30	 — — — —	 mV mV mV mV
V_{CMPOh}	Output high	V_{DD} – 0.5	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay[2]	—	—	40	μs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	μA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD}–0.6 V.
2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to CMP_DACCR[DACEN], CMP_DACCR[VRSEL], CMP_DACCR[VOSEL], CMP_MUXCR[PSEL], and CMP_MUXCR[MSEL]) and the comparator output settling to a stable level.
3. 1 LSB = $V_{reference}$/64

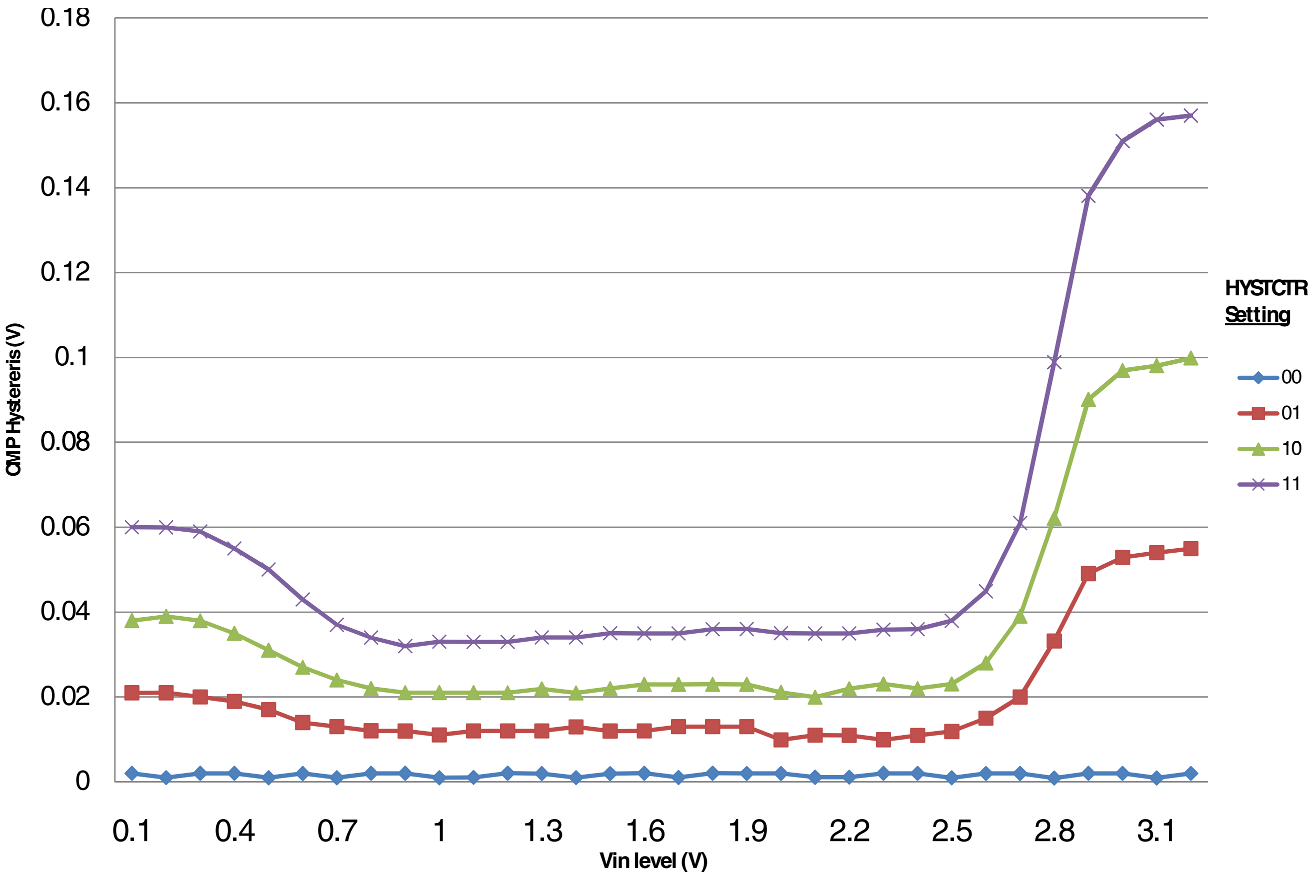

Figure 13. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 1)

6.6.3 12-bit DAC electrical characteristics

6.6.3.1 12-bit DAC operating requirements

Table 27. 12-bit DAC operating requirements

Symbol	Desciption	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
V_{DACR}	Reference voltage	1.13	3.6	V	1
T_A	Temperature	Operating temperature range of the device		°C	
C_L	Output load capacitance	—	100	pF	2
I_L	Output load current	—	1	mA	

1. The DAC reference can be selected to be V_{DDA} or the voltage output of the VREF module (VREF_OUT)
2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC

6.6.3.2 12-bit DAC operating behaviors

Table 28. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA_DACLP}	Supply current — low-power mode	—	—	330	μA	
I_{DDA_DACHP}	Supply current — high-speed mode	—	—	1200	μA	
t_{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	μs	1
t_{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	μs	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	μs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFF	V_{DACR} −100	—	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	—	±8	LSB	2
DNL	Differential non-linearity error — V_{DACR} > 2 V	—	—	±1	LSB	3
DNL	Differential non-linearity error — V_{DACR} = VREF_OUT	—	—	±1	LSB	4
V_{OFFSET}	Offset error	—	±0.4	±0.8	%FSR	5
E_G	Gain error	—	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, $V_{DDA} \geq 2.4$ V	60	—	90	dB	
T_{CO}	Temperature coefficient offset voltage	—	3.7	—	μV/C	6
T_{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
Rop	Output resistance (load = 3 kΩ)	—	—	250	Ω	
SR	Slew rate -80h→ F7Fh→ 80h				V/μs	
	• High power (SP_{HP})	1.2	1.7	—		
	• Low power (SP_{LP})	0.05	0.12	—		
CT	Channel to channel cross talk	—	—	-80	dB	
BW	3dB bandwidth				kHz	
	• High power (SP_{HP})	550	—	—		
	• Low power (SP_{LP})	40	—	—		

1. Settling within ±1 LSB
2. The INL is measured for 0 + 100 mV to V_{DACR} −100 mV
3. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV
4. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV with V_{DDA} > 2.4 V
5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} − 100 mV
6. V_{DDA} = 3.0 V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_C0:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

Table 34. Slave mode DSPI timing (limited voltage range) (continued)

Num	Description	Min.	Max.	Unit
DS10	DSPI_SCK input high/low time	(t_{SCK}/2) − 2	(t_{SCK}/2) + 2	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	10	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	2	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	$\overline{\text{DSPI\_SS}}$ active to DSPI_SOUT driven	—	14	ns
DS16	$\overline{\text{DSPI\_SS}}$ inactive to DSPI_SOUT not driven	—	14	ns

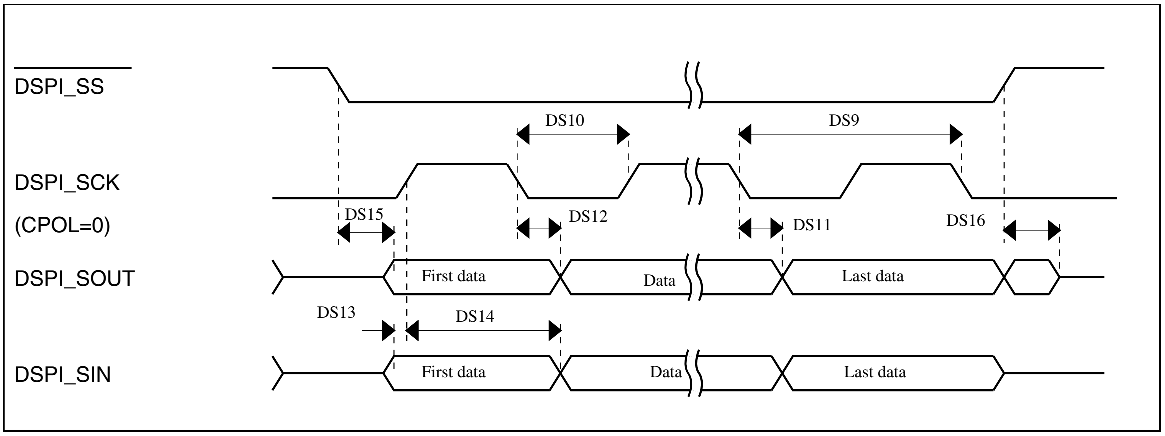

Figure 17. DSPI classic SPI timing — slave mode

6.8.2 DSPI switching specifications (full voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provides DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 35. Master mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	1.71	3.6	V	1
	Frequency of operation	—	12.5	MHz	
DS1	DSPI_SCK output cycle time	4 x t_{BUS}	—	ns	
DS2	DSPI_SCK output high/low time	(t_{SCK}/2) - 4	($t_{SCK/2}$) + 4	ns	
DS3	DSPI_PCS*n* valid to DSPI_SCK delay	(t_{BUS} x 2) − 4	—	ns	2

Table continues on the next page...

Table 37. I2S/SAI master mode timing (continued)

Num.	Characteristic	Min.	Max.	Unit
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	25	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

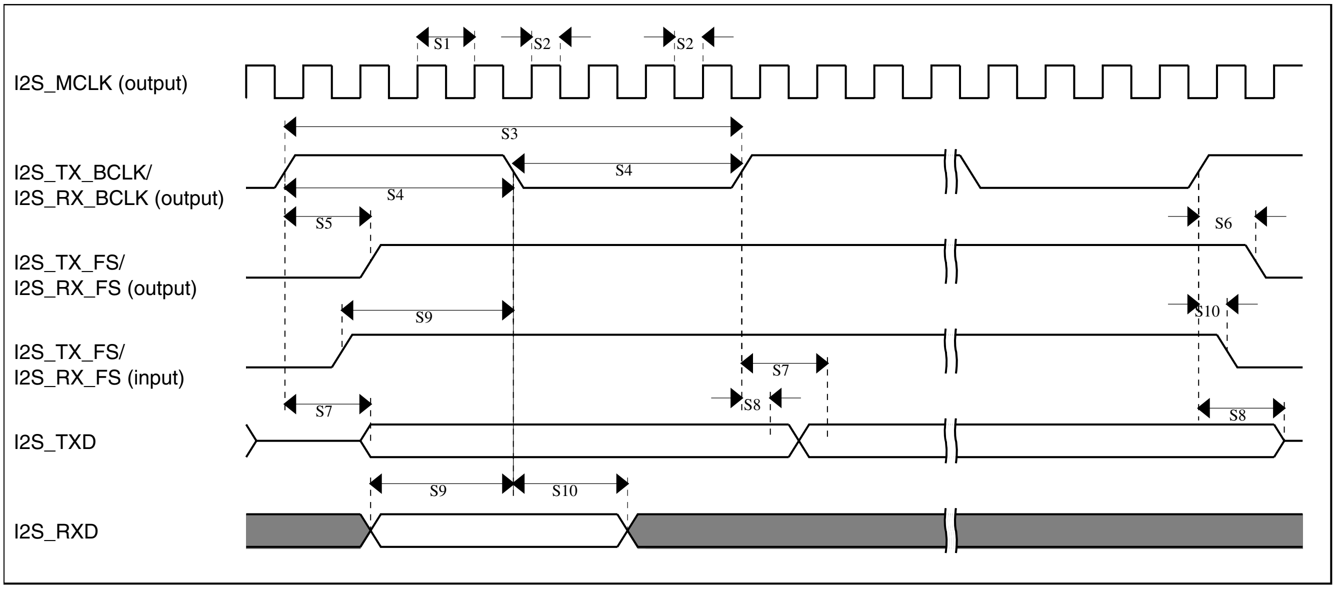

Figure 20. I2S/SAI timing — master modes

Table 38. I2S/SAI slave mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	80	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	10	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	29	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	10	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid[1]	—	21	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

121 MAP BGA	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
L1	ADC0_DP3	ADC0_DP3								
L2	ADC0_DM3	ADC0_DM3								
F5	VDDA	VDDA								
G5	VREFH	VREFH								
G6	VREFL	VREFL								
F6	VSSA	VSSA								
L3	VREF_OUT/CMP1_IN5/CMP0_IN5	VREF_OUT/CMP1_IN5/CMP0_IN5								
K5	DAC0_OUT/CMP1_IN3/ADC0_SE23	DAC0_OUT/CMP1_IN3/ADC0_SE23								
L7	TAMPER0/RTC_WAKEUP_B	TAMPER0/RTC_WAKEUP_B								
H5	TAMPER1	TAMPER1								
J5	TAMPER2	TAMPER2								
L4	XTAL32	XTAL32								
L5	EXTAL32	EXTAL32								
K6	VBAT	VBAT								
J6	JTAG_TCLK/SWD_CLK/EZP_CLK		PTA0	UART0_CTS_b/UART0_COL_b	FTM0_CH5				JTAG_TCLK/SWD_CLK	EZP_CLK
H8	JTAG_TDI/EZP_DI		PTA1	UART0_RX	FTM0_CH6				JTAG_TDI	EZP_DI
J7	JTAG_TDO/TRACE_SWO/EZP_DO		PTA2	UART0_TX	FTM0_CH7				JTAG_TDO/TRACE_SWO	EZP_DO
H9	JTAG_TMS/SWD_DIO		PTA3	UART0_RTS_b	FTM0_CH0				JTAG_TMS/SWD_DIO	
J8	NMI_b/EZP_CS_b		PTA4/LLWU_P3		FTM0_CH1				NMI_b	EZP_CS_b
K7	DISABLED		PTA5		FTM0_CH2			I2S0_TX_BCLK	JTAG_TRST_b	
K8	DISABLED		PTA12		FTM1_CH0			I2S0_TXD0	FTM1_QD_PHA	
L8	DISABLED		PTA13/LLWU_P4		FTM1_CH1			I2S0_TX_FS	FTM1_QD_PHB	
K9	DISABLED		PTA14	SPI0_PCS0	UART0_TX			I2S0_RX_BCLK	I2S0_TXD1	
L9	DISABLED		PTA15	SPI0_SCK	UART0_RX			I2S0_RXD0		
J10	DISABLED		PTA16	SPI0_SOUT	UART0_CTS_b/UART0_COL_b			I2S0_RX_FS	I2S0_RXD1	
H10	DISABLED		PTA17	SPI0_SIN	UART0_RTS_b			I2S0_MCLK		
L10	VDD	VDD								
K10	VSS	VSS								
L11	EXTAL0	EXTAL0	PTA18		FTM0_FLT2	FTM_CLKIN0				
K11	XTAL0	XTAL0	PTA19		FTM1_FLT0	FTM_CLKIN1		LPTMR0_ALT1		

121 MAP BGA	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
D1	NC	NC								
E1	NC	NC								

8.2 K11 Pinouts

The below figure shows the pinout diagram for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

	1	2	3	4	5	6	7	8	9	10	11	
A	PTD7	PTD5	PTD4/ LLWU_P14	NC	NC	PTC13	PTC8	PTC4/ LLWU_P8	NC	PTE19	PTE18	A
B	NC	PTD6/ LLWU_P15	PTD3	NC	NC	PTC12	PTC7	PTC3/ LLWU_P7	PTC0	PTB16	PTB12	B
C	NC	NC	PTD2/ LLWU_P13	PTC17	PTC11/ LLWU_P11	PTC10	PTC6/ LLWU_P10	PTC2	PTB19	PTB11	PTB13	C
D	NC	NC	PTD1	PTD0/ LLWU_P12	PTC16	PTC9	PTC5/ LLWU_P9	PTC1/ LLWU_P6	PTB18	PTB10	NC	D
E	NC	PTE2/ LLWU_P1	PTE1/ LLWU_P0	PTE0	VDD	VDD	NC	NC	PTB17	NC	NC	E
F	NC	NC	NC	PTE3	VDDA	VSSA	NC	NC	NC	NC	NC	F
G	NC	NC	VSS	PTE5	VREFH	VREFL	VSS	PTB3	PTB2	PTB1	PTB0/ LLWU_P5	G
H	NC	NC	NC	PTE17	TAMPER1	NC	PTE4/ LLWU_P2	PTA1	PTA3	PTA17	NC	H
J	NC	NC	NC	NC	TAMPER2	PTA0	PTA2	PTA4/ LLWU_P3	NC	PTA16	RESET_b	J
K	ADC0_DP0	ADC0_DM0	PTE16	NC	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	VBAT	PTA5	PTA12	PTA14	VSS	PTA19	K
L	ADC0_DP3	ADC0_DM3	VREF_OUT/ CMP1_IN5/ CMP0_IN5	XTAL32	EXTAL32	VSS	TAMPER0/ RTC_ WAKEUP_B	PTA13/ LLWU_P4	PTA15	VDD	PTA18	L
	1	2	3	4	5	6	7	8	9	10	11	

Figure 24. K11 121 MAPBGA Pinout Diagram

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